

# Low-Voltage CMOS Quad 2-Input XOR Gate

With 5 V-Tolerant Inputs

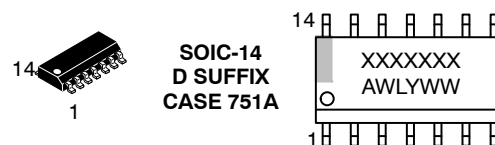
## MC74LCX86

The MC74LCX86 is a high performance, quad 2-input XOR gate operating from a 1.65 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A  $V_I$  specification of 5.5 V allows MC74LCX86 inputs to be safely driven from 5.0 V devices.

### Features

- Designed for 1.65 to 5.5 V  $V_{CC}$  Operation
- 5.0 V Tolerant Inputs – Interface Capability With 5.0 V TTL Logic
- LVTTTL Compatible
- LVC MOS Compatible
- 24 mA Balanced Output Sink and Source Capability @ 3.0 V
- Near Zero Static Supply Current (10  $\mu$ A) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 100 mA
- ESD Performance: Human Body Model >2000 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MARKING DIAGRAMS



XXXXXX = Specific Device Code  
A = Assembly Location  
L, WL = Wafer Lot  
Y, YY = Year  
W, WW = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

MC74LCX86

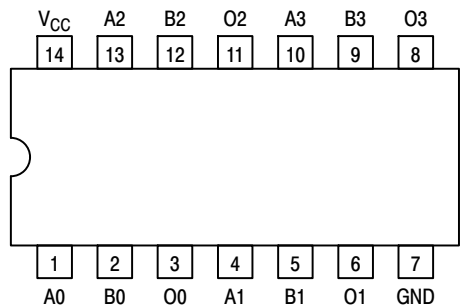


Figure 1. Pinout: 14-Lead (Top View)

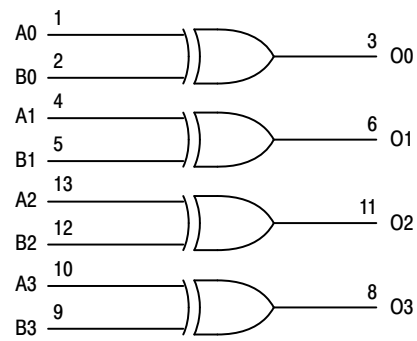


Figure 2. Logic Diagram

PIN NAMES

Pins	Function
An, Bn	Data Inputs
On	Outputs

TRUTH TABLE

Inputs		Outputs
An	Bn	On
L	L	L
L	H	H
H	L	H
H	H	L

# MC74LCX86

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	-0.5 to +6.5	V
$V_I$	DC Input Voltage (Note 1)	-0.5 to +6.5	V
$V_O$	DC Output Voltage (Note 1) Active-Mode (High or Low State) Tri-State Mode Power-Down Mode ( $V_{CC} = 0$ V)	-0.5 to $V_{CC} + 0.5$ -0.5 to +6.5 -0.5 to +6.5	V
$I_{IK}$	DC Input Diode Current $V_I < GND$	-50	mA
$I_{OK}$	DC Output Diode Current $V_O < GND$	-50	mA
$I_O$	DC Output Source/Sink Current	$\pm 50$	mA
$I_{CC}$ or $I_{GND}$	DC Supply Current per Supply Pin or Ground Pin	$\pm 100$	mA
$T_{STG}$	Storage Temperature Range	-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 secs	260	°C
$T_J$	Junction Temperature Under Bias	+150	°C
$\theta_{JA}$	Thermal Resistance (Note 1) SOIC-14 QFN14 TSSOP-14	116 130 150	°C/W
$P_D$	Power Dissipation in Still Air at 125°C SOIC-14 QFN14 TSSOP-14	1077 962 833	mW
MSL	Moisture Sensitivity	Level 1	-
$F_R$	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
$V_{ESD}$	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $I_O$  absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{CC}$	Supply Voltage Operating Data Retention Only	1.65 1.5	3.3 3.3	5.5 5.5	V
$V_I$	Digital Input Voltage	0	-	5.5	V
$V_O$	Output Voltage Active Mode (High or Low State) Tri-State Mode Power Down Mode ( $V_{CC} = 0$ V)	0 0 0	- - -	$V_{CC}$ 5.5 5.5	V
$T_A$	Operating Free-Air Temperature	-40	-	+125	°C
$t_r, t_f$	Input Rise or Fall Rate $V_{CC} = 1.65$ V to 1.95 V $V_{CC} = 2.3$ V to 2.7 V $V_I$ from 0.8 V to 2.0 V, $V_{CC} = 3.0$ V $V_{CC} = 4.5$ V to 5.5 V	0 0 0 0	- - - -	20 20 10 5	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

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## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
				Min	Max	Min	Max	
V <sub>IH</sub>	HIGH Level Input Voltage		1.65 – 1.95	0.65 x V <sub>CC</sub>	–	0.65 x V <sub>CC</sub>	–	V
			2.3 – 2.7	1.7	–	1.7	–	
			3.0 – 3.6	2.0	–	2.0	–	
			4.5 – 5.5	0.70 x V <sub>CC</sub>	–	0.70 x V <sub>CC</sub>	–	
V <sub>IL</sub>	LOW Level Input Voltage		1.65 – 1.95	–	0.35 x V <sub>CC</sub>	–	0.35 x V <sub>CC</sub>	V
			2.3 – 2.7	–	0.7	–	0.7	
			3.0 – 3.6	–	0.8	–	0.8	
			4.5 – 5.5	–	0.30 x V <sub>CC</sub>	–	0.30 x V <sub>CC</sub>	
V <sub>OH</sub>	High-Level Output Voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	1.65 to 5.5	V <sub>CC</sub> – 0.1	–	V <sub>CC</sub> – 0.1	–	V
		I <sub>OH</sub> = –100 µA	1.65	1.29	–	1.29	–	
		I <sub>OH</sub> = –4 mA	2.3	1.8	–	1.8	–	
		I <sub>OH</sub> = –8 mA	2.7	2.2	–	2.2	–	
		I <sub>OH</sub> = –12 mA	3.0	2.4	–	2.4	–	
		I <sub>OH</sub> = –16 mA	3.0	2.2	–	2.2	–	
		I <sub>OH</sub> = –32 mA	4.5	3.7	–	3.7	–	
V <sub>OL</sub>	Low-Level Output Voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>	1.65 to 5.5	–	0.1	–	0.1	V
		I <sub>OL</sub> = 100 µA	1.65	–	0.24	–	0.24	
		I <sub>OL</sub> = 4 mA	2.3	–	0.3	–	0.3	
		I <sub>OL</sub> = 8 mA	2.7	–	0.4	–	0.4	
		I <sub>OL</sub> = 12 mA	3.0	–	0.4	–	0.4	
		I <sub>OL</sub> = 16 mA	3.0	–	0.55	–	0.55	
		I <sub>OL</sub> = 32 mA	4.5	–	0.6	–	0.6	
I <sub>I</sub>	Input Leakage Current	V <sub>I</sub> = 0 to 5.5 V	3.6	–	±5.0	–	±5.0	µA
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>I</sub> = 5.5 V or V <sub>O</sub> = 5.5 V	0	–	10	–	10	µA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>I</sub> = 5.5 V or GND	3.6	–	10	–	10	µA
ΔI <sub>CC</sub>	Increase in I <sub>CC</sub> per Input	V <sub>IH</sub> = V <sub>CC</sub> – 0.6 V	2.3 to 3.6	–	500	–	500	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
				Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, Input to Output	See Figures 3 and 4	1.65 to 1.95	–	12.0	–	12.0	ns
			2.3 to 2.7	–	7.8	–	7.0	
			2.7	–	7.0	–	7.0	
			3.0 to 3.6	–	6.5	–	6.5	
			4.5 to 5.5	–	4.5	–	4.5	

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## AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
				Min	Max	Min	Max	
t <sub>OSHL</sub> , t <sub>OSLH</sub>	Output to Output Skew		1.65 to 1.95	–	–	–	–	ns
			2.3 to 2.7	–	–	–	–	
			2.7	–	–	–	–	
			3.0 to 3.6	–	1.0	–	1.0	
			4.5 to 5.5	–	–	–	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## DYNAMIC SWITCHING CHARACTERISTICS

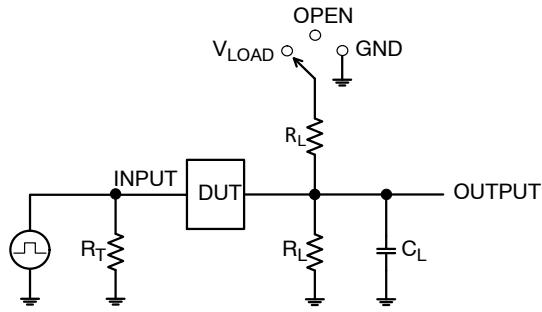
Symbol	Characteristic	Condition	T <sub>A</sub> = +25 °C			Unit
			Min	Typ	Max	
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 5)	V <sub>CC</sub> = 3.3 V, C <sub>L</sub> = 50 pF, V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V		0.8		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 5)	V <sub>CC</sub> = 3.3 V, C <sub>L</sub> = 50 pF, V <sub>IH</sub> = 3.3 V, V <sub>IL</sub> = 0 V		0.8		V

5. Number of outputs defined as “n”. Measured with “n-1” outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typ	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	7	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>CC</sub> = 3.3 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, V <sub>CC</sub> = 3.3 V, V <sub>I</sub> = 0 V or V <sub>CC</sub>	25	pF

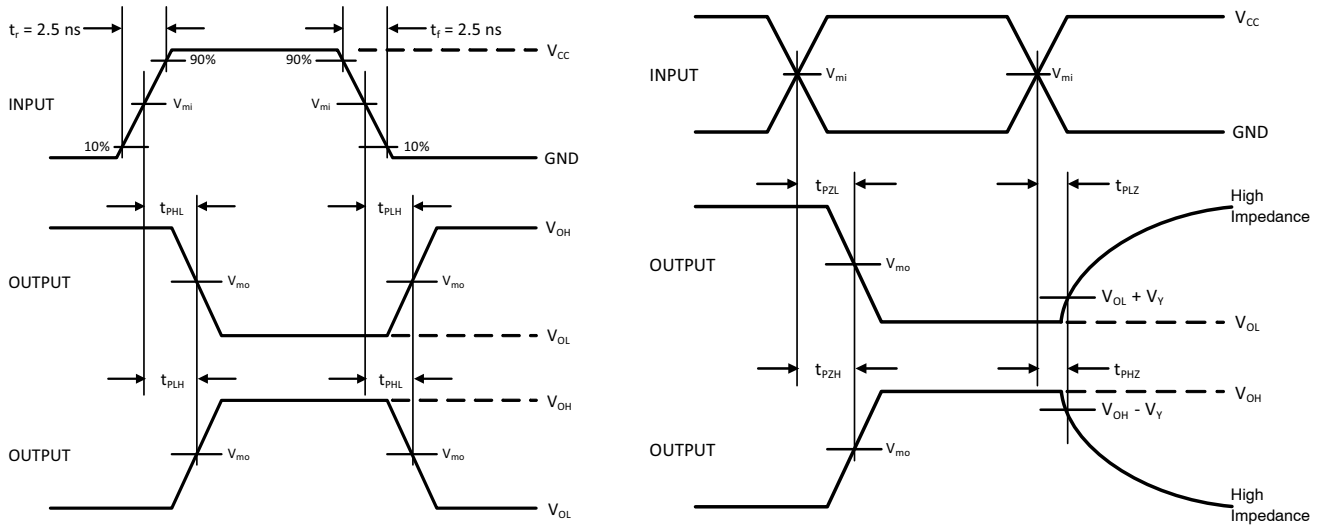
## MC74LCX86



$C_L$  includes probe and jig capacitance  
 $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )  
 $f = 1$  MHz

Test	Switch Position
$t_{PLH} / t_{PHL}$	Open
$t_{PLZ} / t_{PZL}$	$V_{LOAD}$
$t_{PHZ} / t_{PZH}$	GND

Figure 3. Test Circuit



$V_{CC}$ , V	$R_L$ , $\Omega$	$C_L$ , pF	$V_{LOAD}$	$V_m$ , V	$V_Y$ , V
1.65 to 1.95	500	30	$2 \times V_{CC}$	$V_{CC}/2$	0.15
2.3 to 2.7	500	30	$2 \times V_{CC}$	$V_{CC}/2$	0.15
2.7	500	50	6 V	1.5	0.3
3.0 to 3.6	500	50	6 V	1.5	0.3
4.5 to 5.5	500	50	$2 \times V_{CC}$	$V_{CC}/2$	0.3

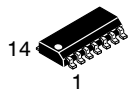
Figure 4. Switching Waveforms

### ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
MC74LCX86DR2G	LCX86G	SOIC-14	2500 / Tape & Reel
MC74LCX86DTR2G	LCX86	TSSOP-14	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

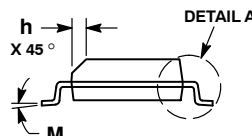
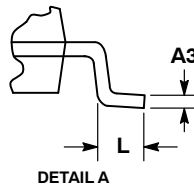
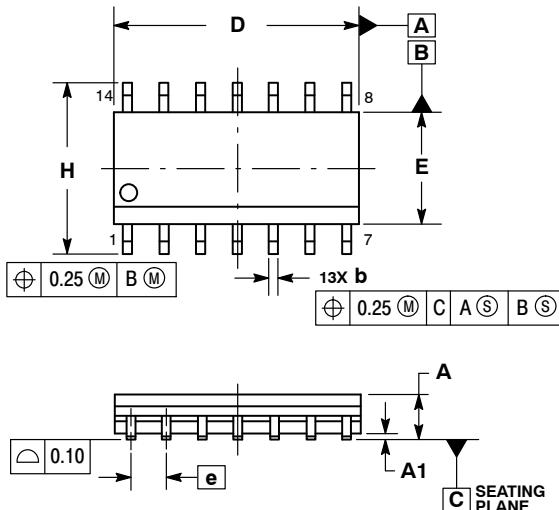
\*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.



SCALE 1:1

SOIC-14 NB  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016

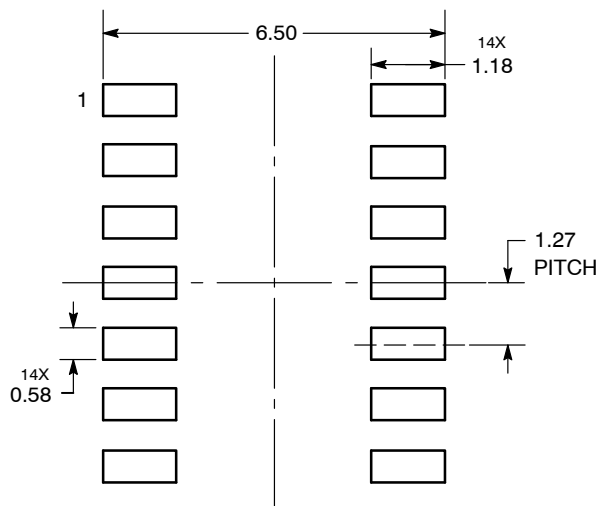


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

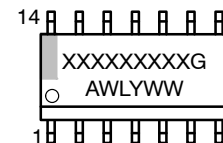
SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC  
MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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**SOIC-14**  
**CASE 751A-03**  
**ISSUE L**

DATE 03 FEB 2016

STYLE 1:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. NO CONNECTION  
5. ANODE/CATHODE  
6. NO CONNECTION  
7. ANODE/CATHODE  
8. ANODE/CATHODE  
9. ANODE/CATHODE  
10. NO CONNECTION  
11. ANODE/CATHODE  
12. ANODE/CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 2:  
CANCELLED

STYLE 3:  
PIN 1. NO CONNECTION  
2. ANODE  
3. ANODE  
4. NO CONNECTION  
5. ANODE  
6. NO CONNECTION  
7. ANODE  
8. ANODE  
9. ANODE  
10. NO CONNECTION  
11. ANODE  
12. ANODE  
13. NO CONNECTION  
14. COMMON CATHODE

STYLE 4:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. CATHODE  
4. NO CONNECTION  
5. CATHODE  
6. NO CONNECTION  
7. CATHODE  
8. CATHODE  
9. CATHODE  
10. NO CONNECTION  
11. CATHODE  
12. CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 5:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. ANODE/CATHODE  
5. ANODE/CATHODE  
6. NO CONNECTION  
7. COMMON ANODE  
8. COMMON CATHODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. ANODE/CATHODE  
12. ANODE/CATHODE  
13. NO CONNECTION  
14. COMMON ANODE

STYLE 6:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE  
4. CATHODE  
5. CATHODE  
6. CATHODE  
7. CATHODE  
8. ANODE  
9. ANODE  
10. ANODE  
11. ANODE  
12. ANODE  
13. ANODE  
14. ANODE

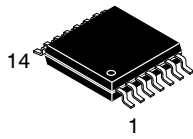
STYLE 7:  
PIN 1. ANODE/CATHODE  
2. COMMON ANODE  
3. COMMON CATHODE  
4. ANODE/CATHODE  
5. ANODE/CATHODE  
6. ANODE/CATHODE  
7. ANODE/CATHODE  
8. ANODE/CATHODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. COMMON CATHODE  
12. COMMON ANODE  
13. ANODE/CATHODE  
14. ANODE/CATHODE

STYLE 8:  
PIN 1. COMMON CATHODE  
2. ANODE/CATHODE  
3. ANODE/CATHODE  
4. NO CONNECTION  
5. ANODE/CATHODE  
6. ANODE/CATHODE  
7. COMMON ANODE  
8. COMMON ANODE  
9. ANODE/CATHODE  
10. ANODE/CATHODE  
11. NO CONNECTION  
12. ANODE/CATHODE  
13. ANODE/CATHODE  
14. COMMON CATHODE

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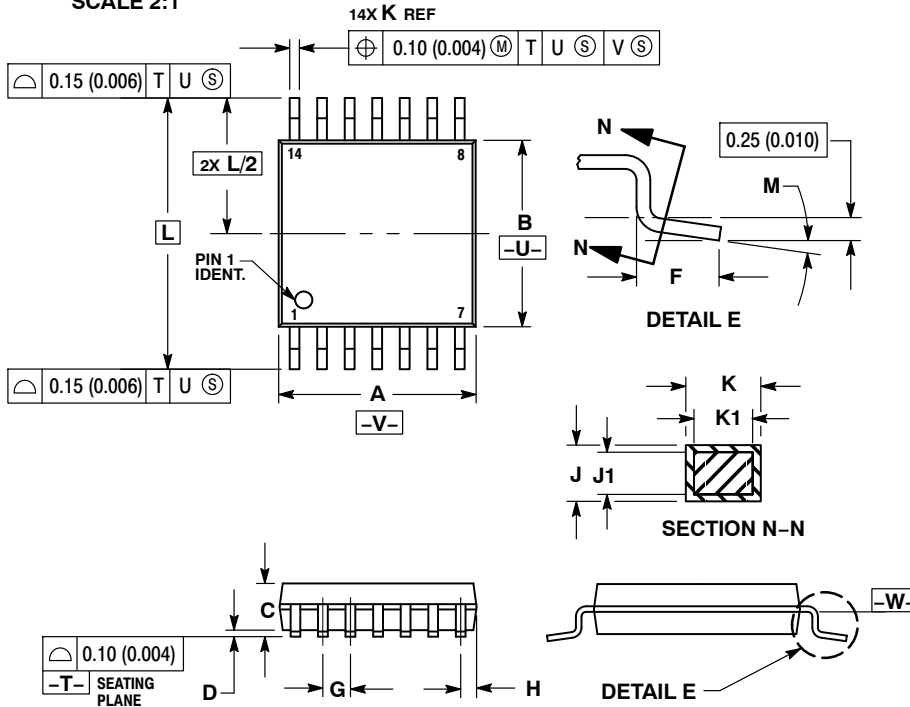
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**TSSOP-14 WB**  
CASE 948G  
ISSUE C

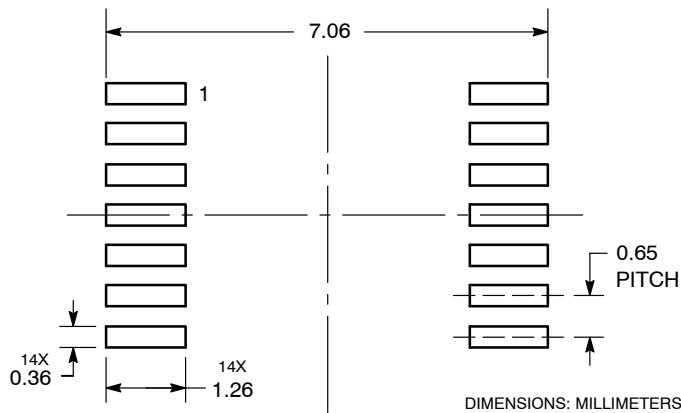
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SCALE 2:1

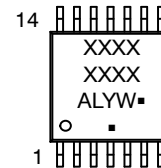

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**RECOMMENDED  
SOLDERING FOOTPRINT\***


\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC  
MARKING DIAGRAM\***


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▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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**DESCRIPTION:** TSSOP-14 WB

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